



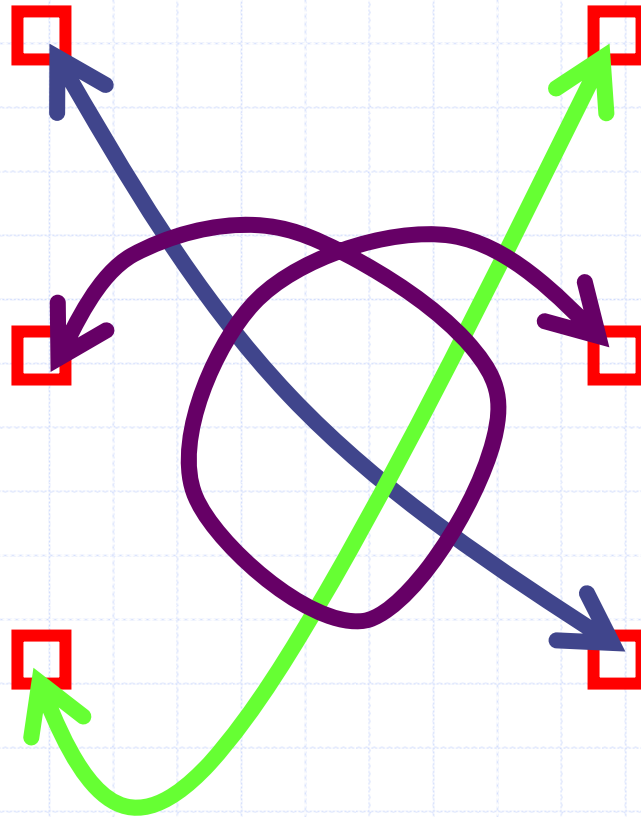
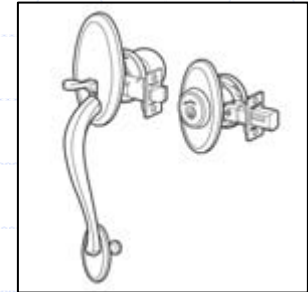
Model to Hardware Matching for nm Scale Technologies

Sani R. Nassif Manager Tools & Technology Department

IBM Research – Austin

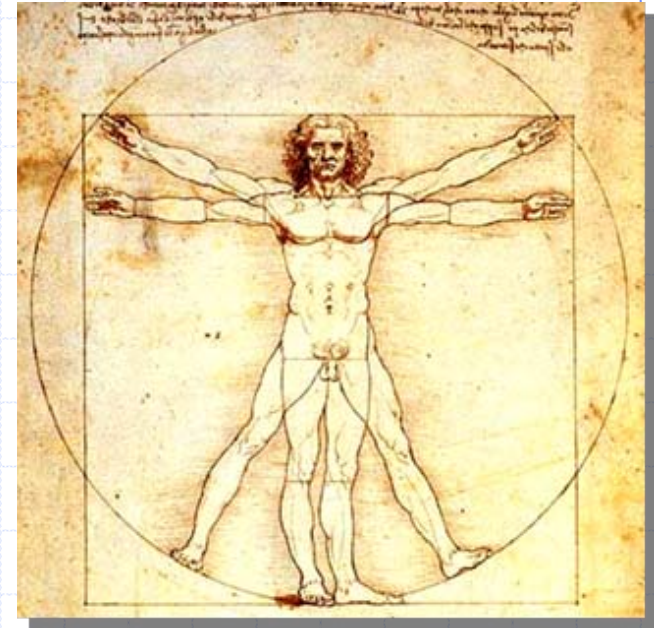
nassif@us.ibm.com

Model to Hardware Matching?



DFM Job Description

- ◆ What is the real problem?
- ◆ Imagine 10^9 people being asked to form a human chain.
 - Maybe the population of Europe.
 - With height and width of each person varying by $\sim 50\%$.
 - Maybe after some beer...
- ◆ This is what we ask 1B highly variable MOSFETs to do!
 - And we want to predict how long the chain is going to be, and how much food and beer is required etc...
- ◆ And... we cannot prototype!
We use predictive models, and need them to match reality.

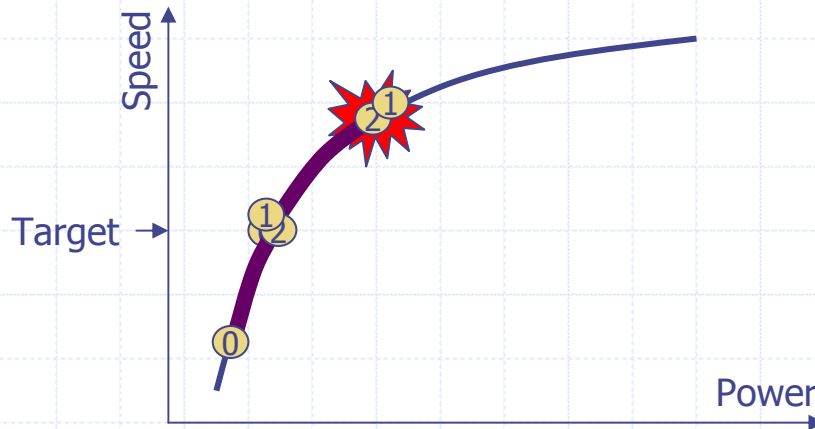
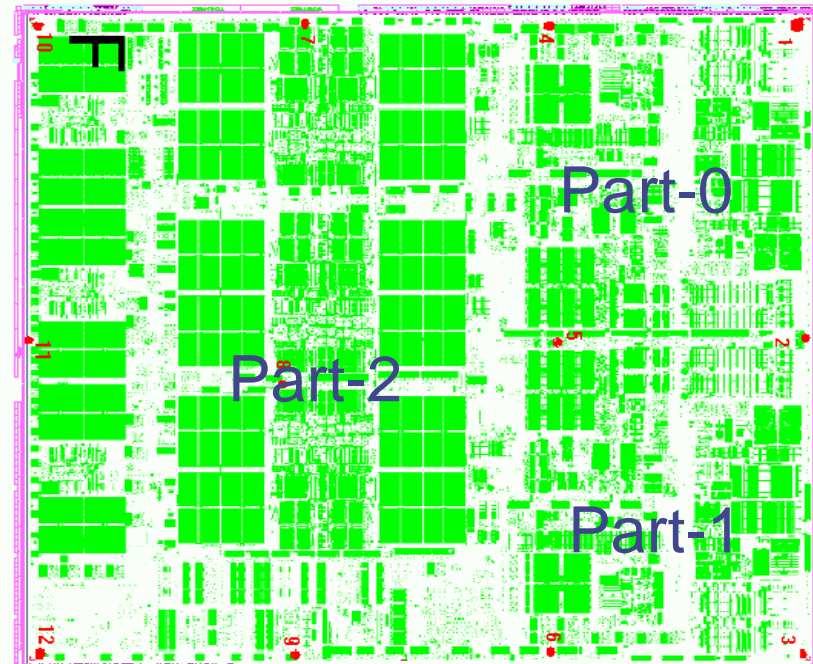


Realities and Motivation

- ◆ The IC industry is built on a foundation of models for performance, power, yield, cost...
- ◆ When models do not predict the correct outcome, we lose money.
- ◆ Technology complexity near the end of scaling is exacerbating this “prediction gap”.
- ◆ Investments in technology modeling and understanding are needed!

An Example from IBM

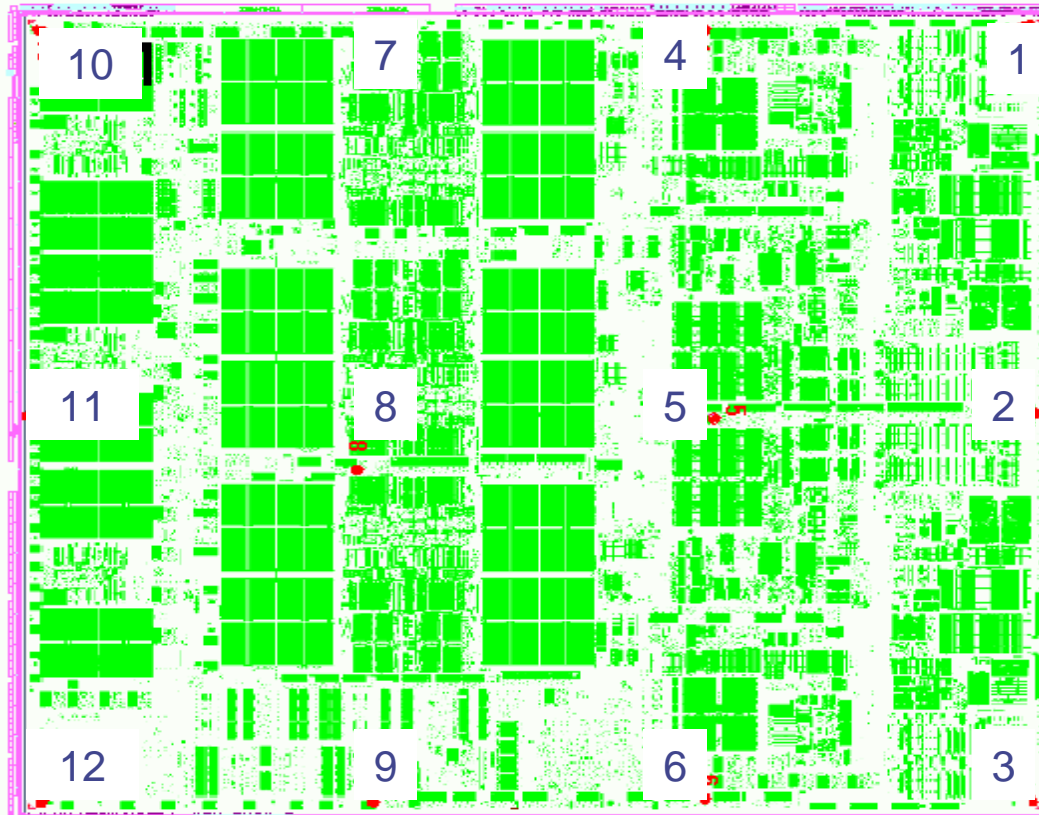
- ◆ One part of a design was found to be $\sim 15\%$ slower than other parts.
- ◆ Models predict all parts of design are identical.
- ◆ Model/hardware mismatch!
 - Slower block limits F_{MAX} .
 - Faster block wastes power.



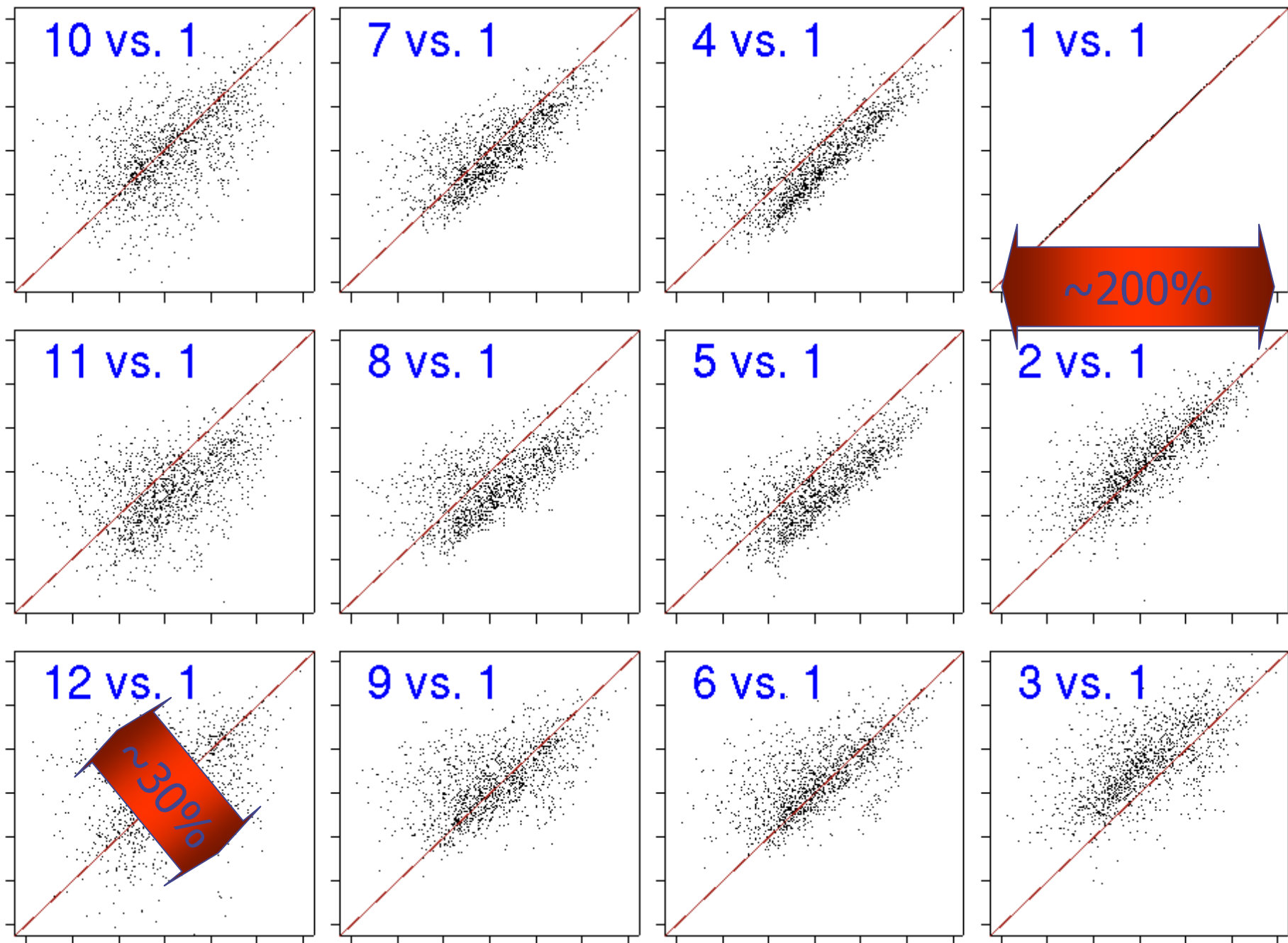
Case study performed by
Anne E. Gattiker

Model to Hardware Support

- ◆ Chip has 12 ring oscillators distributed across the die, and individually measurable.

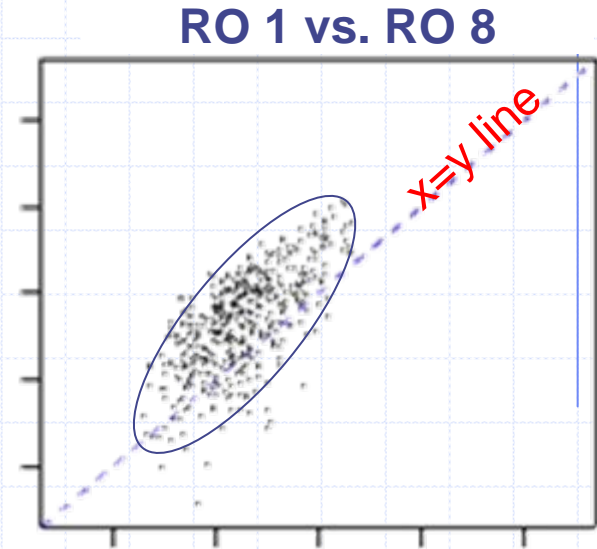


Chip map with Ring Oscillator locations



Systematic Offsets

- ◆ Strong correlations between:
 - Part-0 and RO 1.
 - Part-2 and RO 8.



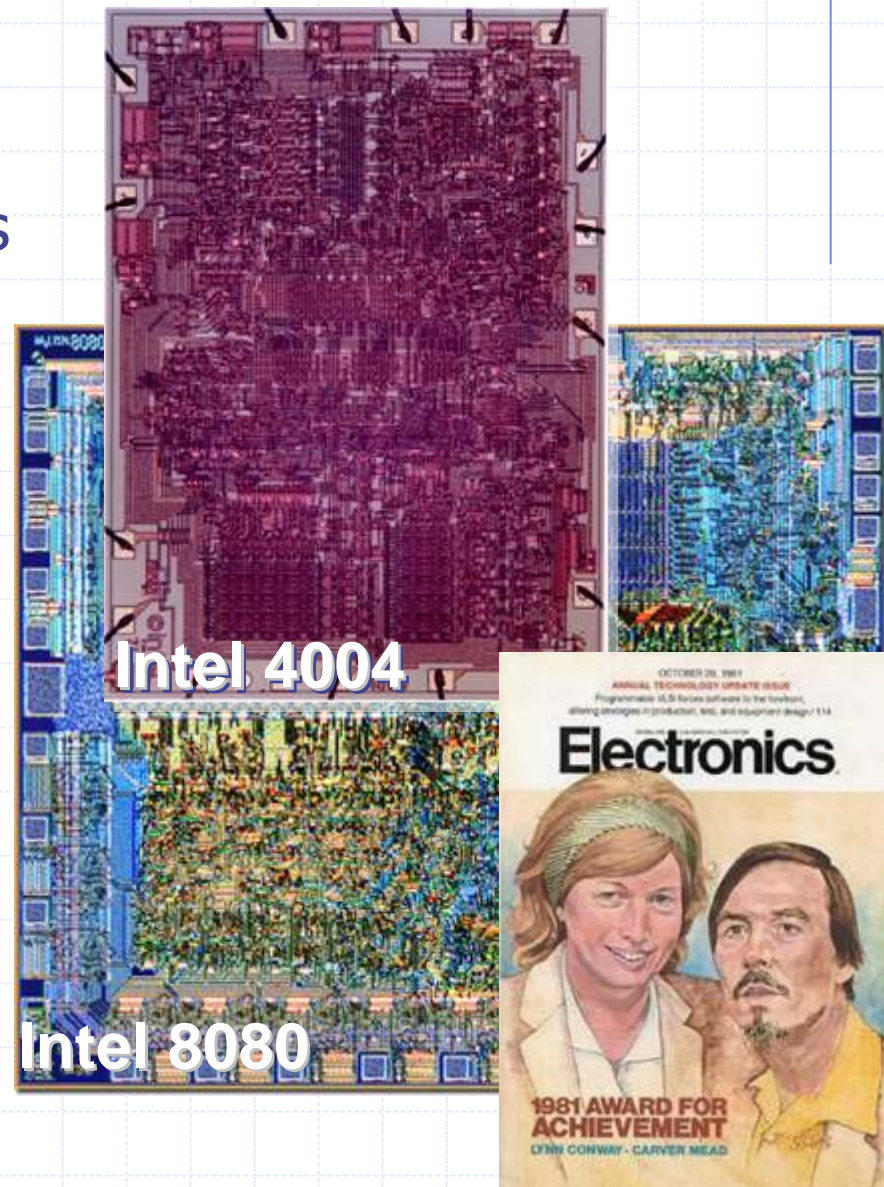
- ◆ Systematic offset between the ROs.
 - Even though the two ROs are identical!

Conclusion:

- ◆ Within-die variability caused systematic spatial mismatch (mean shift + rotation).
- ◆ Magnitude of mismatch large and has –ve impact on design.

Why? (Historical Perspective)

- ◆ In the beginning, design was hard and only few were able to do it well. This was the age of “chip engineering”.
- ◆ But with scaling-driven performance, it became possible to abstract design to a few simple rules. This was the age of “chip computer science”!

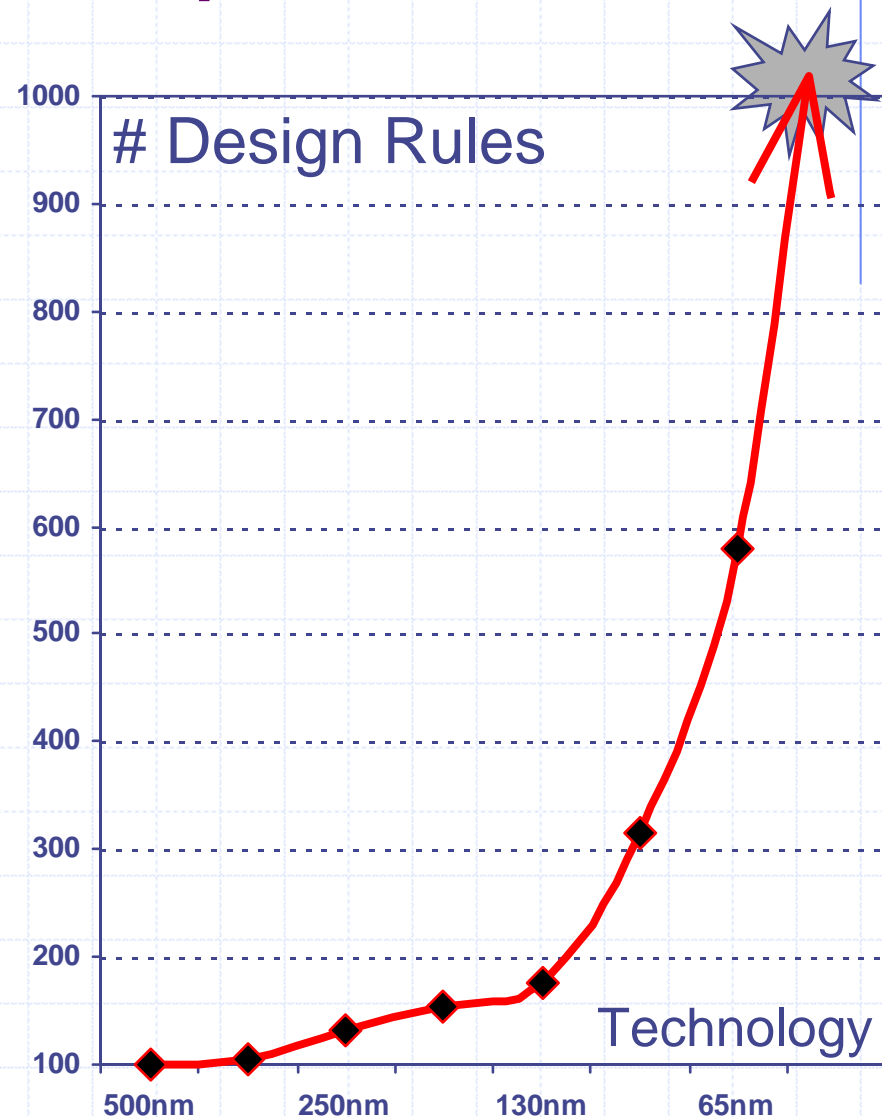


Technology Complexity

Technology has become so complex that it is not well represented by "rules".

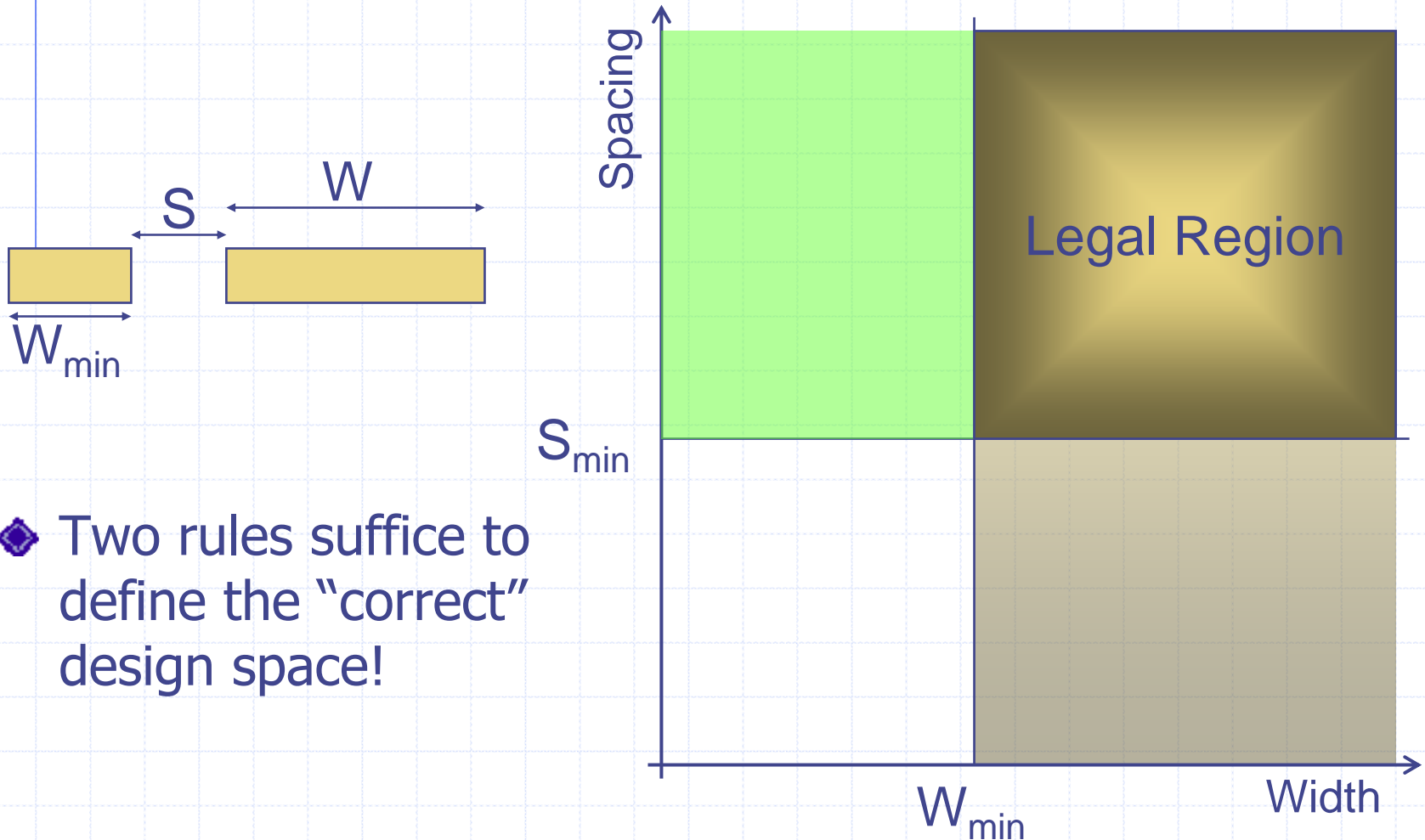
Design / Technology interface information bandwidth needs are skyrocketing!

Expressing complex non-linear realities via rules is becoming difficult.



Technology Rules (History)

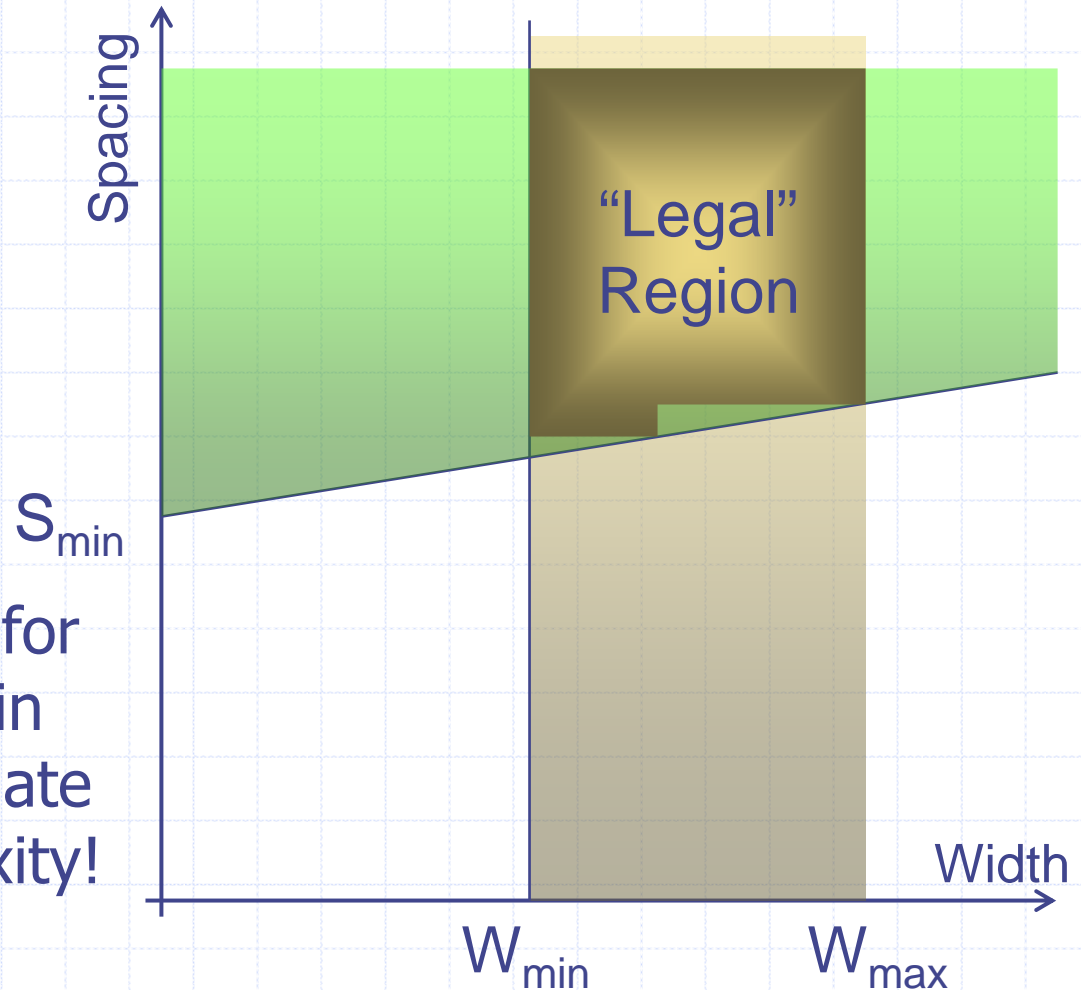
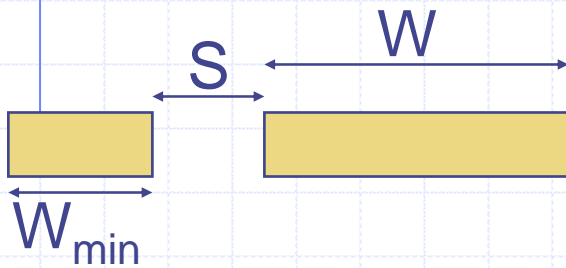
◆ Example: wire spacing...



◆ Two rules suffice to define the "correct" design space!

Technology Rule Explosion

◆ Impact of CMP, Dishing, Erosion as well as lithography...



◆ Four (or more) rules for the same situation in order to accommodate technology complexity!

What Does This Change?

- ◆ Transistor performance is being determined by new physics and complex interactions.
 - Large variety in behaviors.
 - Systematic & Random variability increasing.
- ◆ Devices used for technology characterization becoming less typical...
 - Number of variants is exploding.
 - Ability to bound all behaviors is compromised.
- ◆ Result: model / hardware mismatch.
 - Gap in our understanding of technology is relatively large and getting larger!

Where Does This Put Us?

- ◆ Our lack of understanding of technology is endangering the way we do design.
- ◆ The “contract” between manufacturing and design can no longer be just BSIM+DRC.
- ◆ These changes will have a dramatic impact on CAD and on the Foundry business.
 - More than just more OPC.
- ◆ Much of what we observe is being driven by variability...

Variability vs. Uncertainty

- ◆ **Variability**: known quantitative relationship to a source (readily modeled and simulated) – **systematic!**
 - Designer has option to *null* out impact.
 - Example: power delivery (package + grid) noise.
 - ◆ **Uncertainty**: sources unknown, or model too difficult/costly to generate or simulate – **random!**
 - Usually treated by some type of worst-case analysis.
 - Example: ΔV_{TH} within die variation.
- ◆ Lack of modeling infrastructure and/or resources often transforms variability to uncertainty.
- Example: power grid noise when not assessed!

Taxonomy

- ◆ In addition to systematic and random, we also differentiate variability according to source and distribution.

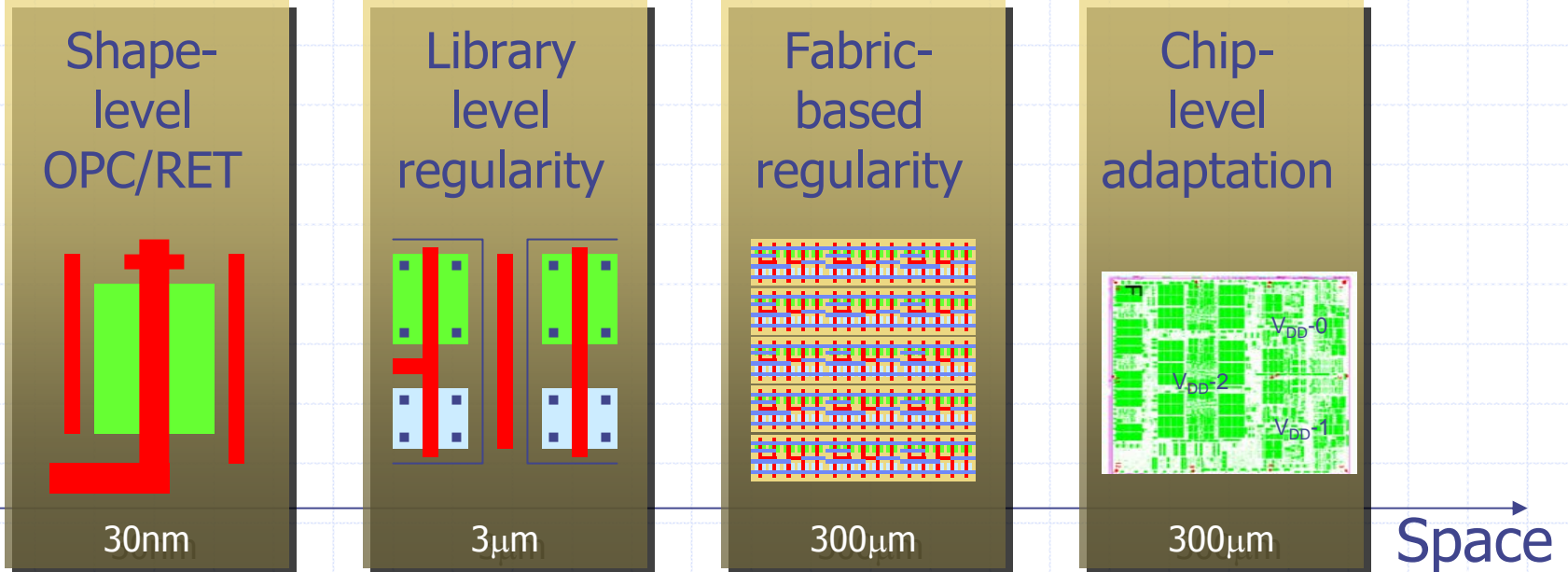
	Physical (time scale 10^9 sec)	Environmental (time scale 10^{-9} sec)
Spatial	$\Delta L, \Delta \mu, \Delta V_T$	Noise coupling
Temporal	NBTI, Hot- \bar{e} , electro-migration	V_{DD}, T

Variability Interaction with Design

- ◆ Old view: Die to die variation dominant
 - **Imposed** upon design (constant regardless of design).
 - Predominantly random (e.g. wafer location effect).
 - Well modeled via worst-case files.
- ◆ New view: Within-die variation dominant
 - **Co-generated** between design & process (depend on details of the design).
 - Predominantly systematic.
 - Example: CMP-driven RC variation.

Response to Variability

- ◆ Responses to variability target different “spatial frequencies”.
 - No one response is sufficient to tackle the full impact, but all responses require accurate estimates of magnitude and impact.



Variability Characterization

- ◆ A hard problem.
- ◆ Requires a large investment in test and characterization in order to understand all aspects of physical, environmental, systematic, random, etc...
- ◆ Also, many factors are design dependent.
 - So often generic test structures are not useful predictors (e.g. analog circuits)!
 - Number of variants exploding with “transistor weight” problem.

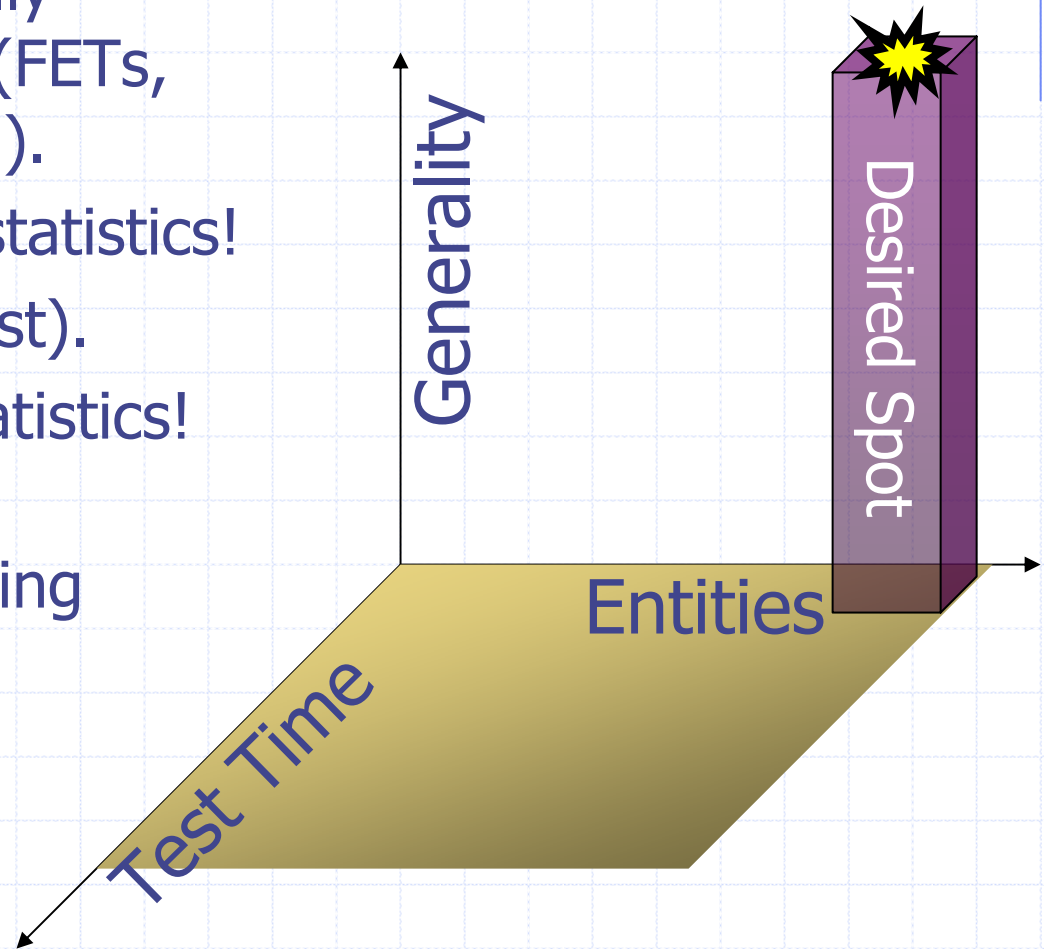
Silicon Information Density

- ◆ The efficiency with which we can perform precise variability characterization is going to become important.
 - No longer sufficient to do it once (technology bring up). Need to continually model and re-evaluate.
 - As EDA tools ramp up on understanding process, they will enable new methods of design optimization (e.g. during re-spins).
- ◆ Need vastly more information from scarce Si & test resources (i.e. more density)!

Test Structure Quality?

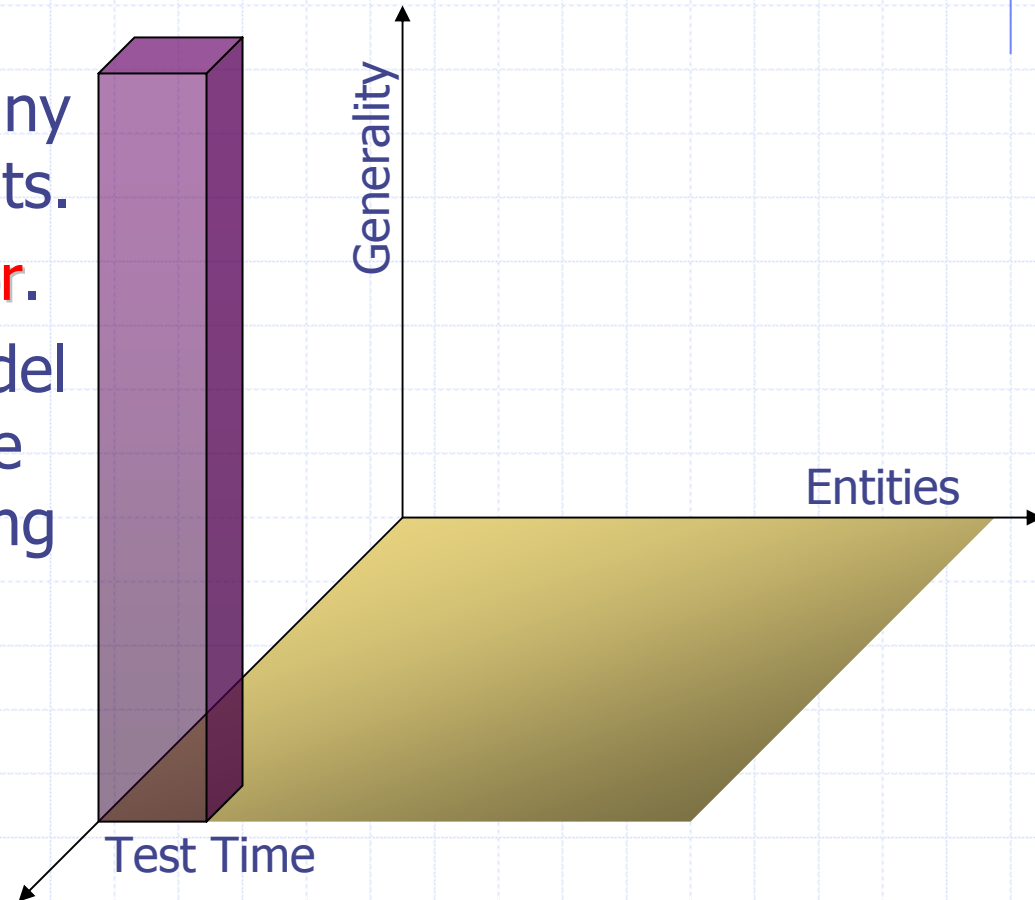
Three relative measures:

- ◆ Number of individually measurable entities (FETs, ring oscillators, etc...)
 - Many entities \Rightarrow statistics!
- ◆ Test time (or test cost).
 - Lower cost \Rightarrow statistics!
- ◆ Generality of result: suitability for predicting design outcome.
 - Modeling & EDA.



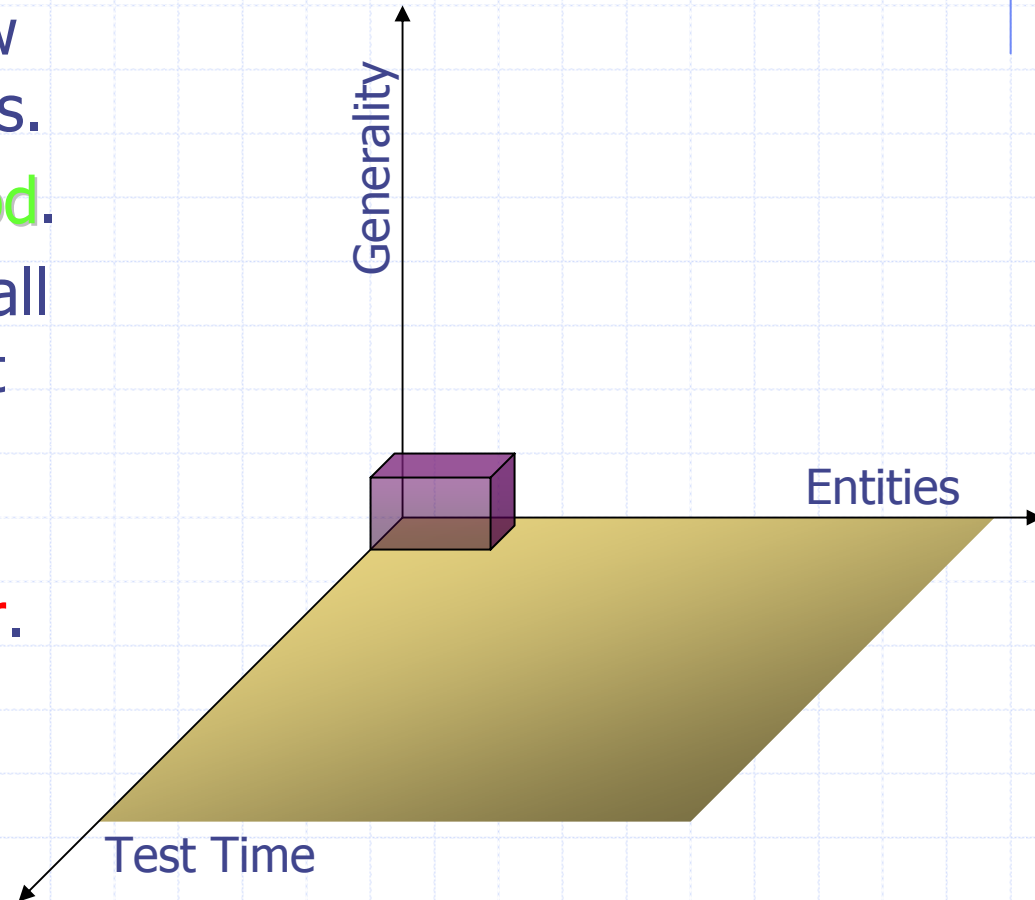
Example: Device Characterization

- ◆ Small number of devices with various dimensions.
 - Entities **poor**.
- ◆ Typically measure many current / voltage points.
 - Slow test time **poor**.
- ◆ Used to generate model parameters, which are the basis for everything else... (e.g. BSIM)
 - i.e. generality **excellent**.



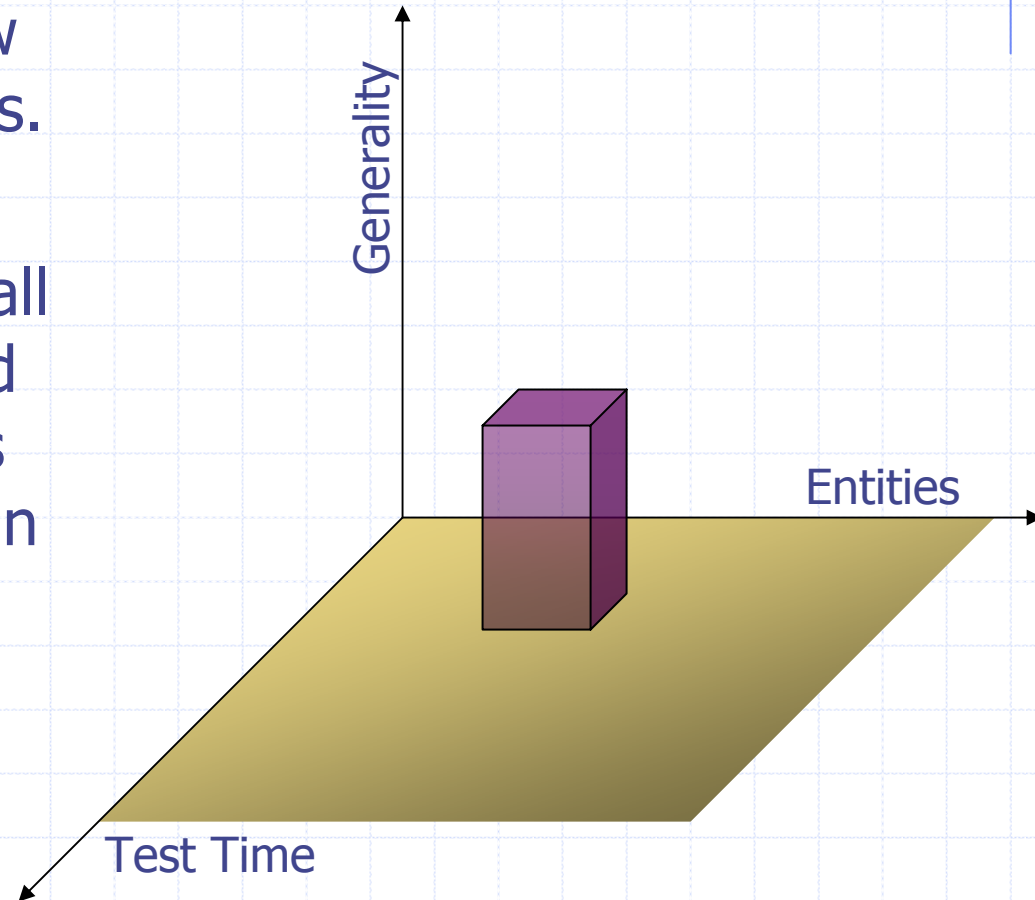
Example: Ring Oscillators (ROs)

- ◆ Few ROs per unit.
 - Entities **poor**.
- ◆ Typically measure few frequency & I_{DD} points.
 - Fast test time, **good**.
- ◆ Useful to assess overall health of process, but result is unique to RO structure.
 - i.e. generality **poor**.

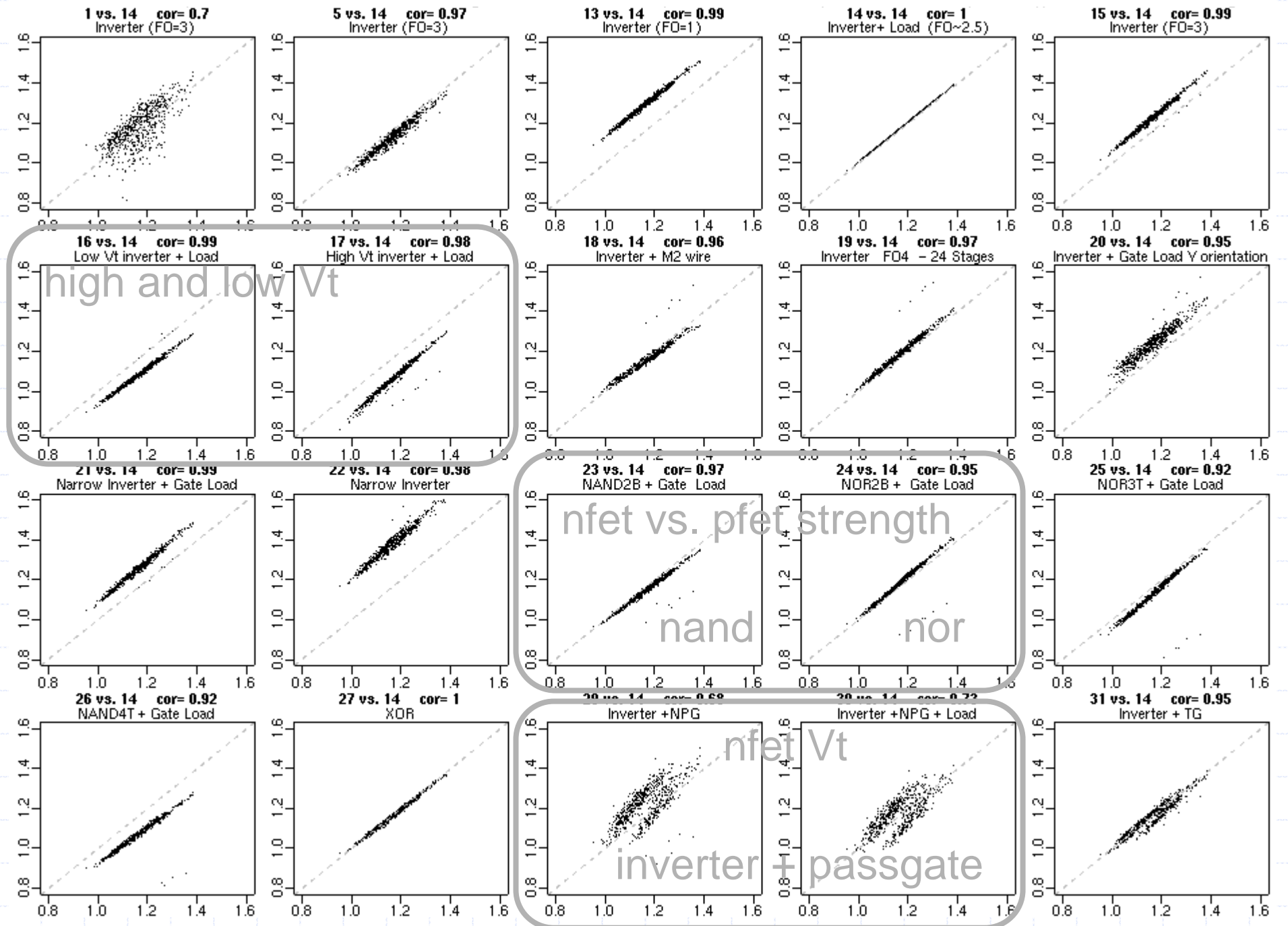


Example: RO Collections

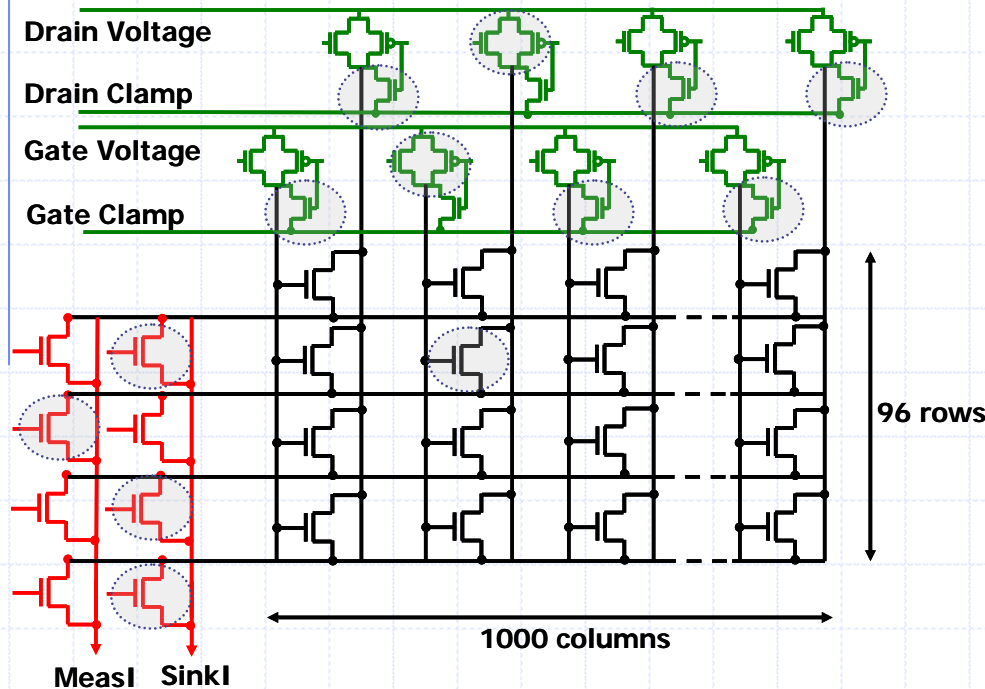
- ◆ Variety of ROs per unit.
 - Entities OK.
- ◆ Typically measure few frequency & I_{DD} points.
 - Test good.
- ◆ Useful to assess overall health of process, and since a variety of ROs are included, more can be learned.
 - i.e. generality OK.



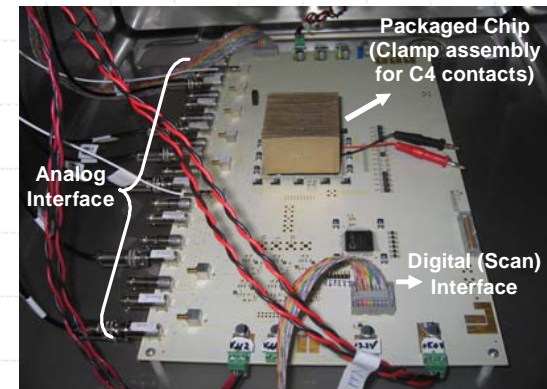
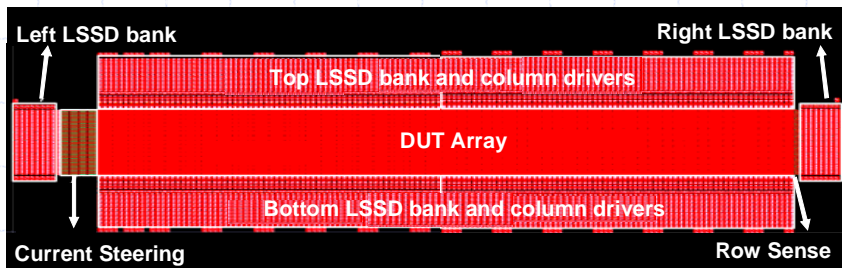
Canonical view: Varied ring types versus basic inverter ring



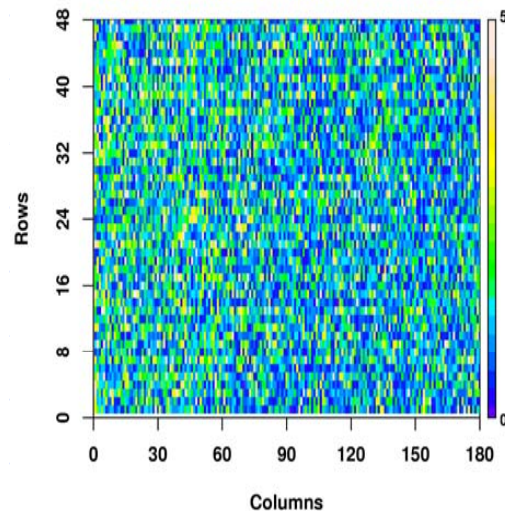
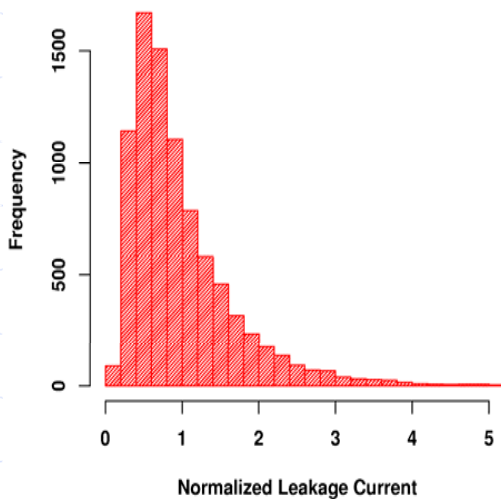
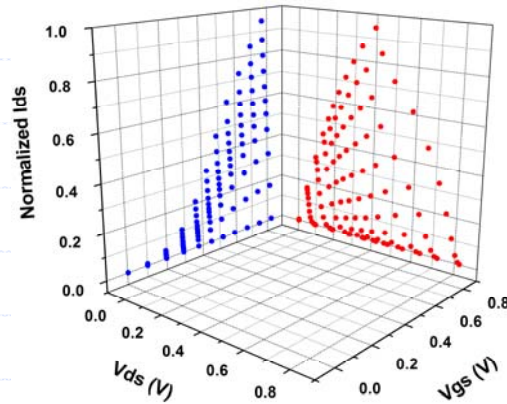
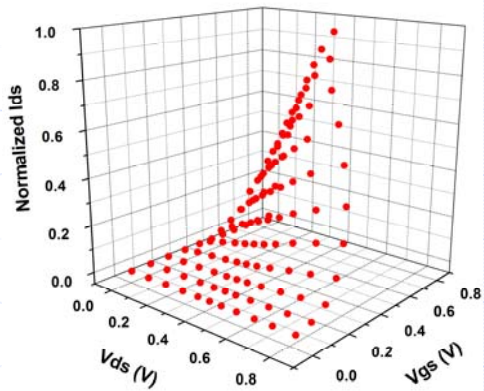
Advanced Modeling Structure



- ◆ SRAM sized devices arranged in an addressable manner.
- ◆ 96 rows, 1000 columns – 96,000 total devices.
- ◆ Complete I/V possible.



Experimental Results



- ◆ Measure full I/V range.
 - Extract parameter statistics through least-squares based parameter extraction.
- ◆ Leakage statistics.
 - Lognormal distribution.
 - No spatial correlation.
 - Systematic effects do not appear due to regular layout.
 - Random dopant effect is the dominant source of variation.

Siren Call: Variational Modeling

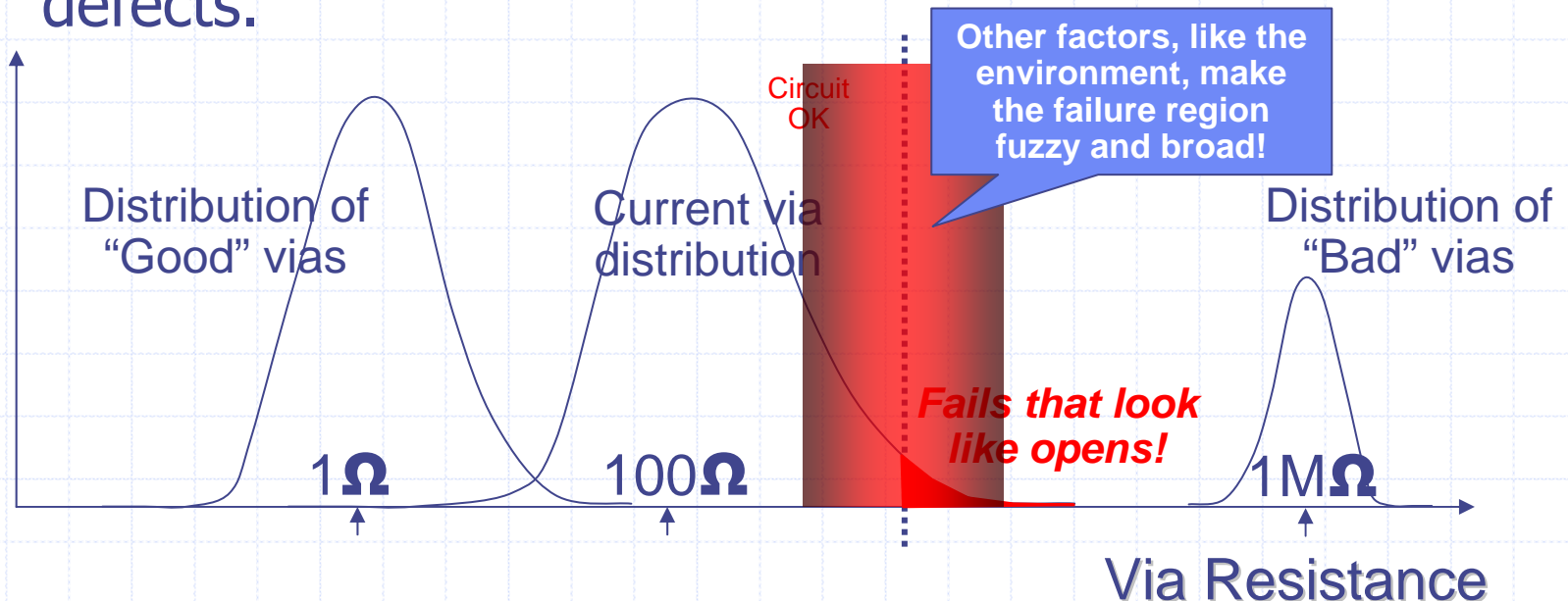
- ◆ Device models caught between the need to provide nominal and statistical accuracy.
- ◆ Nominal accuracy: ever more complex models with many fitting parameters and difficult-to-extract inter-dependencies.
 - Can you spell BSIM?
- ◆ Statistical accuracy: simple models that exhibit a physically significant and predictive correlation structure.
 - **What is the right solution for this?**

Linking Variability & Resilience

- ◆ Much current work is focused on the immediate and short term impact of variability.
 - Examples: statistical timing analysis, CMP-aware routing, new approaches for function-based OPC etc...
- ◆ But increasing variability will change the **character** of the impact it has on circuits.

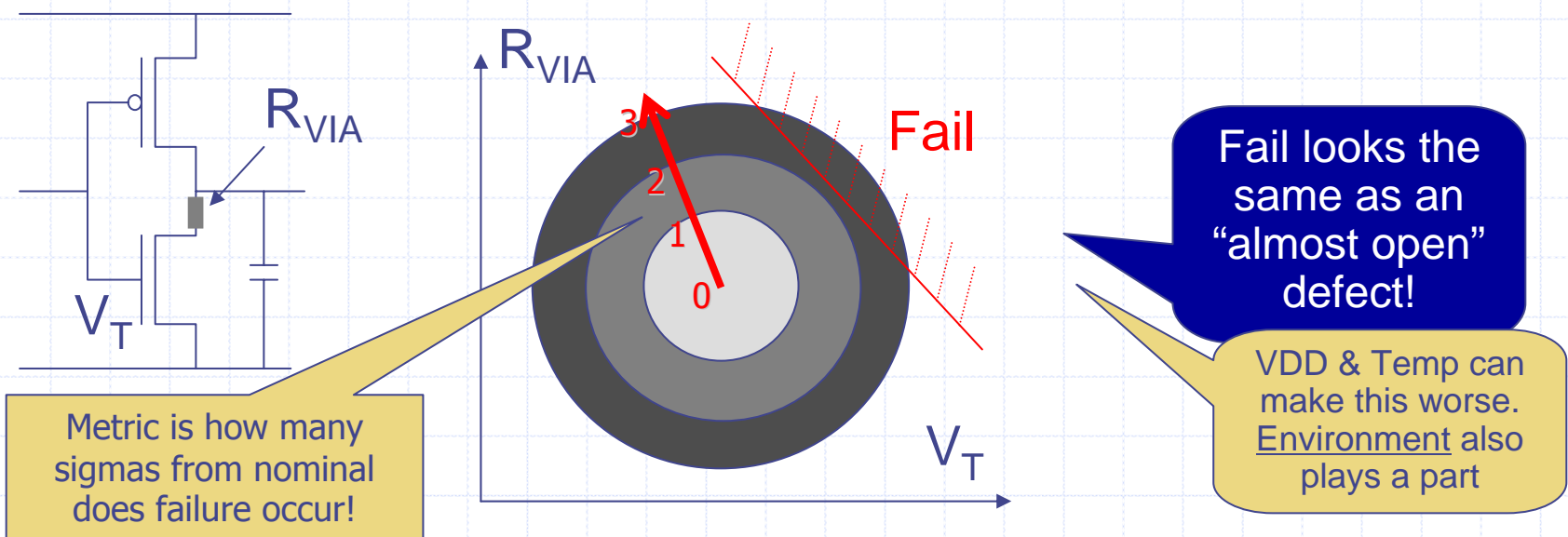
What changes with increased variability?

- ◆ Circuits can become permanently or intermittently defective.
- ◆ Failure dependence on operating environment makes test coverage very difficult to achieve.
- ◆ This can be viewed as the merger of failure modes due to structural (topological), and parametric (variability) defects.

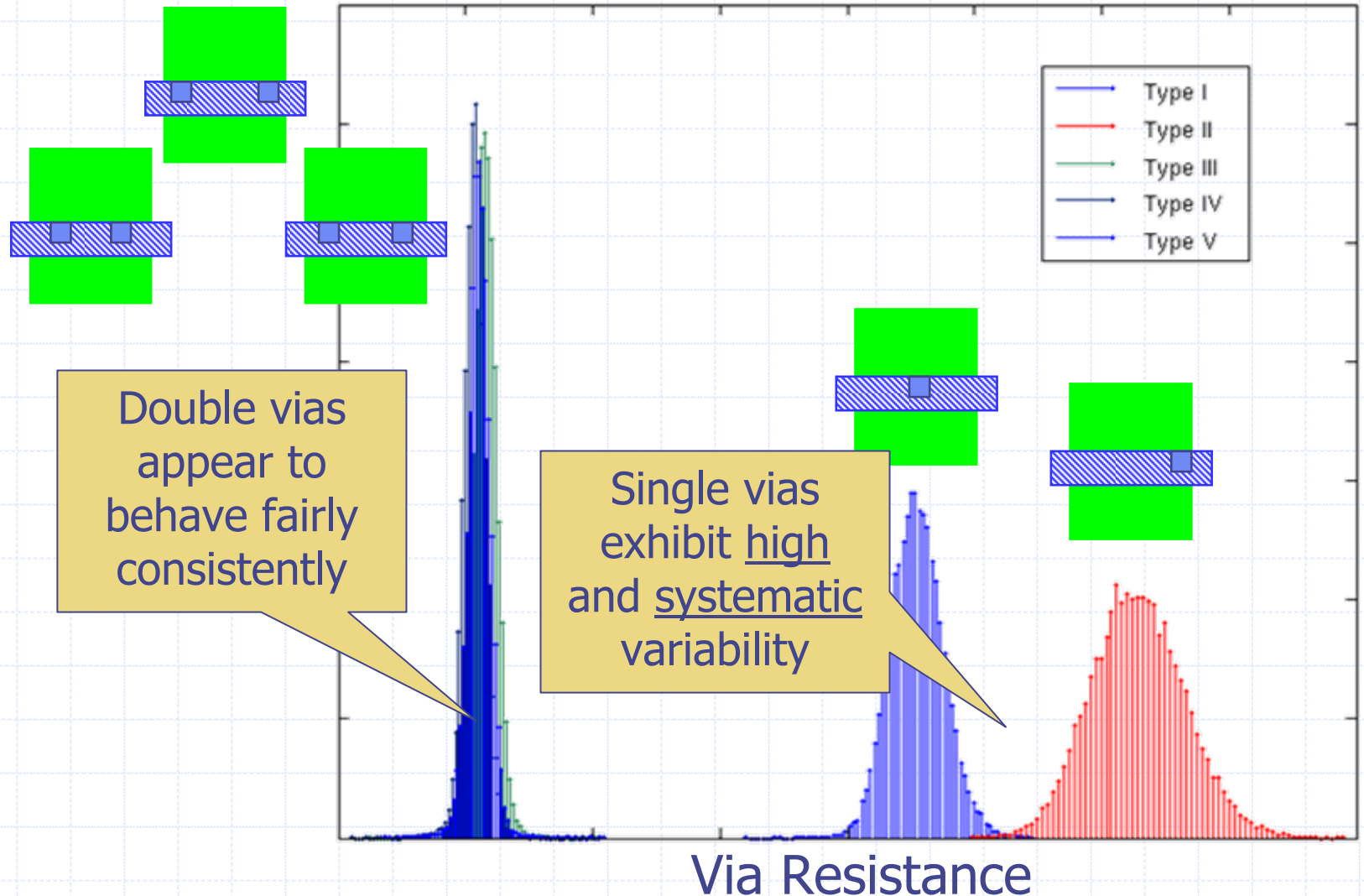


How Is This Happening?

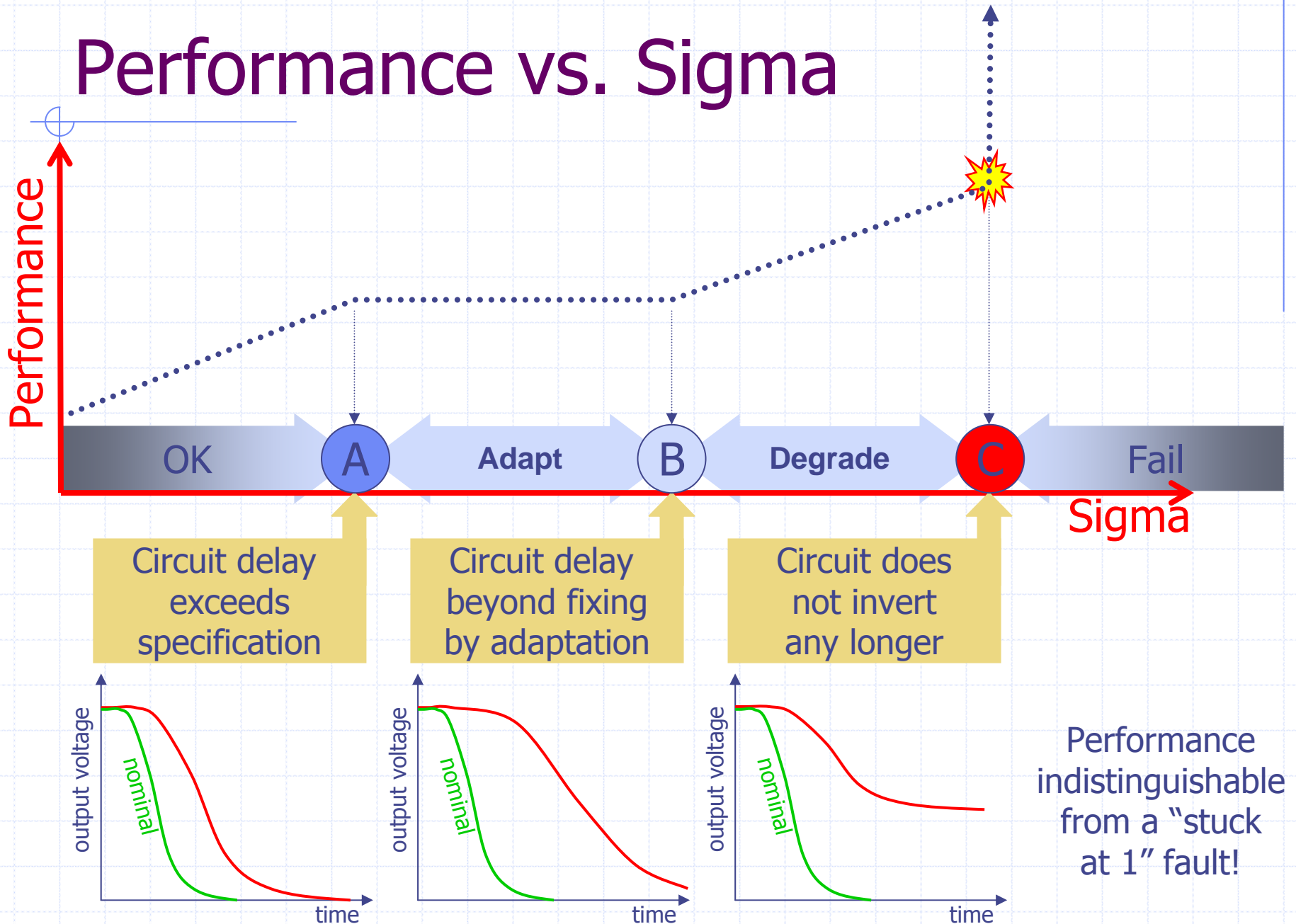
- ◆ Increased process complexity and systematic variability.
 - Example: a V_T of 0.25 ± 0.1 , a via of $20 \dots 200 \Omega$.
 - Multidimensional: combination of multiple sources of variations.
- ◆ As variability increases, circuit performance passes from a degraded phase to a regime where failure becomes indistinguishable from hard (short/open) faults.



Random/Systematic Via Variability



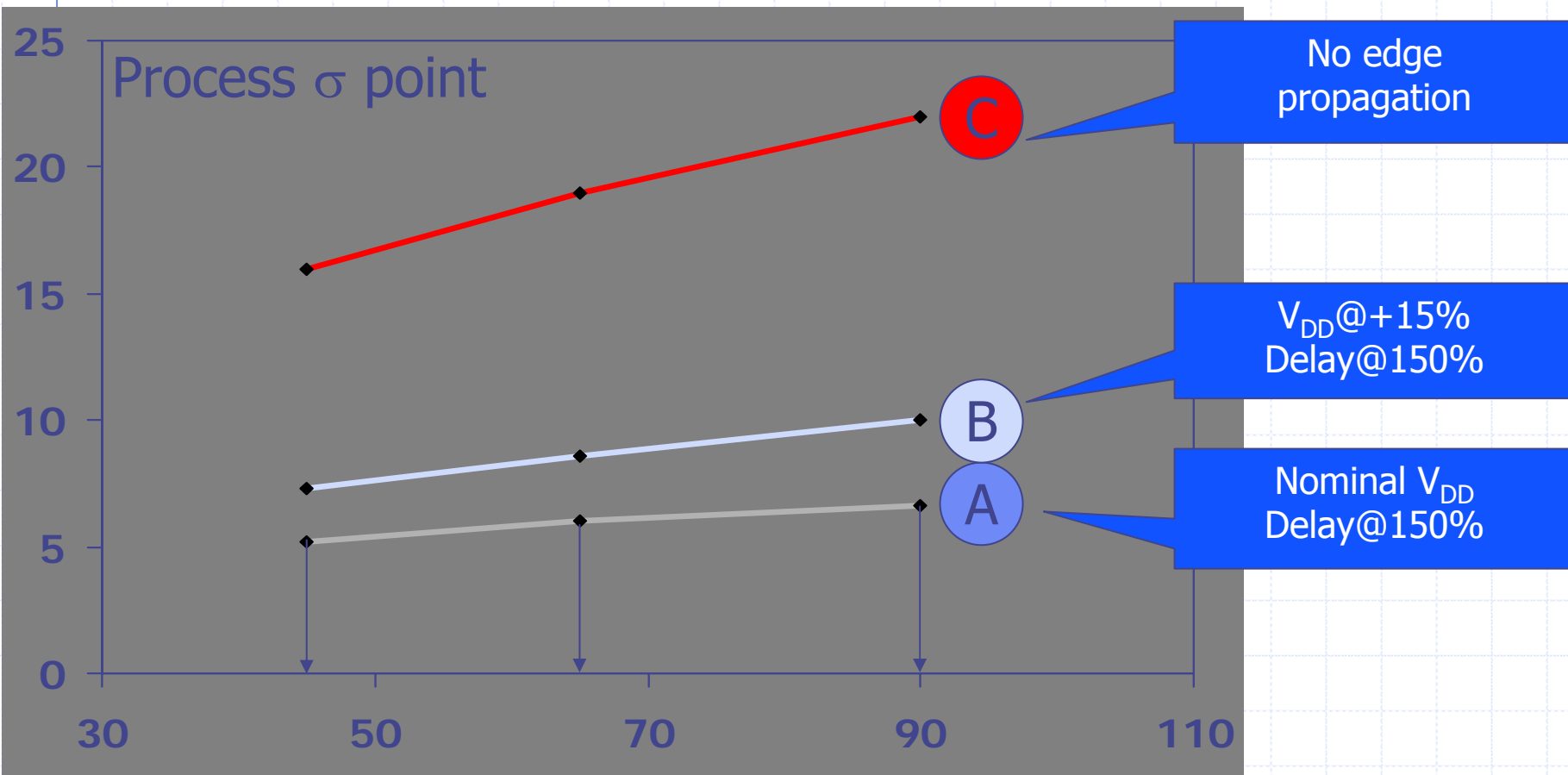
Performance vs. Sigma



Performance indistinguishable from a "stuck at 1" fault!

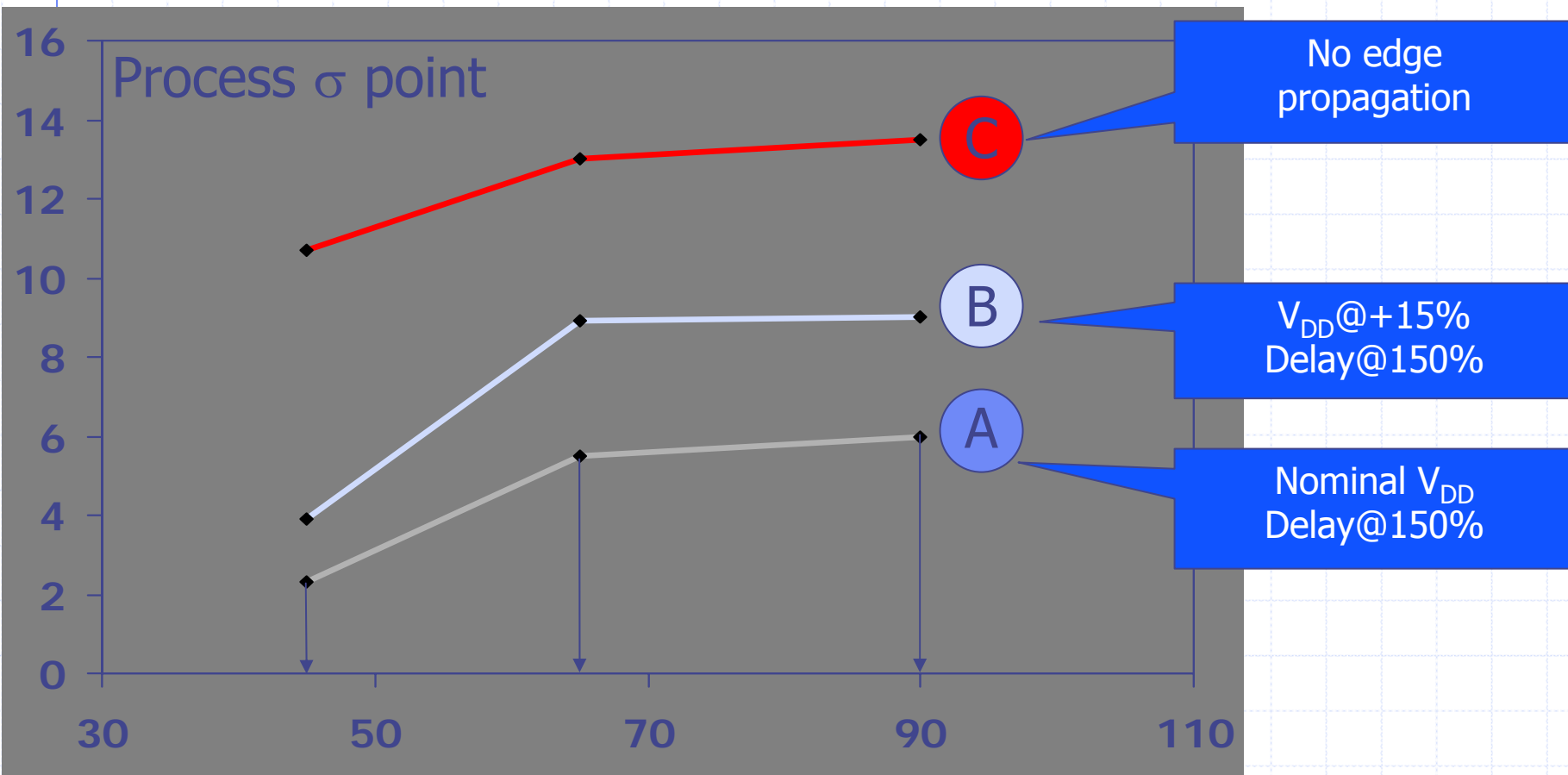
Trend For a Simple Buffer

- ◆ Simplest possible circuit (if this fails, everything else will).
- ◆ Performed analysis for 90nm, 65nm and 45nm.
- ◆ Clear trend in sigma!



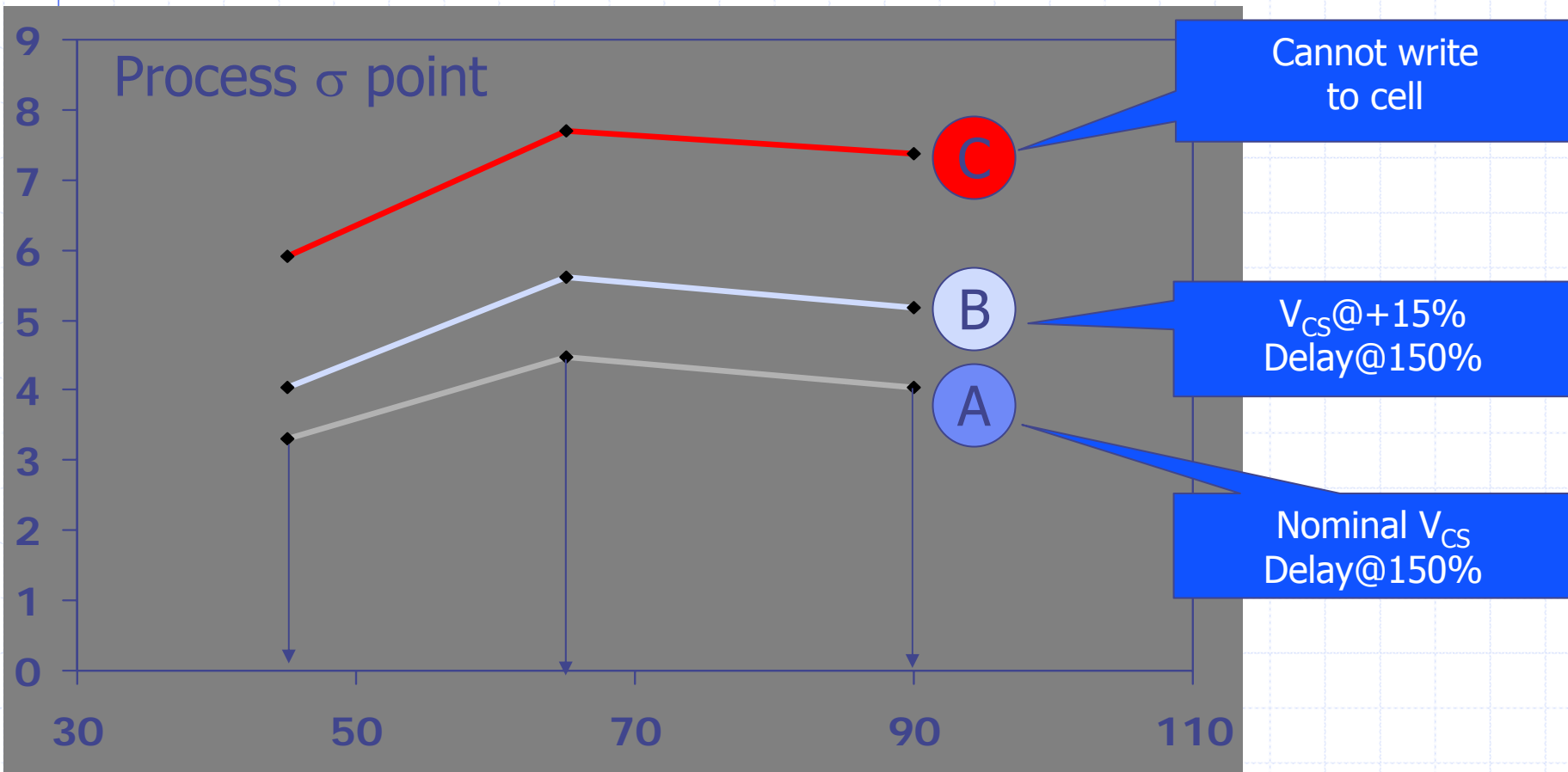
Technology Trend For a Simple Latch

- ◆ Pervasive circuit crucial for correct logic operation.
- ◆ Performed analysis for 90nm, 65nm and 45nm.
- ◆ Clear trend in sigma!



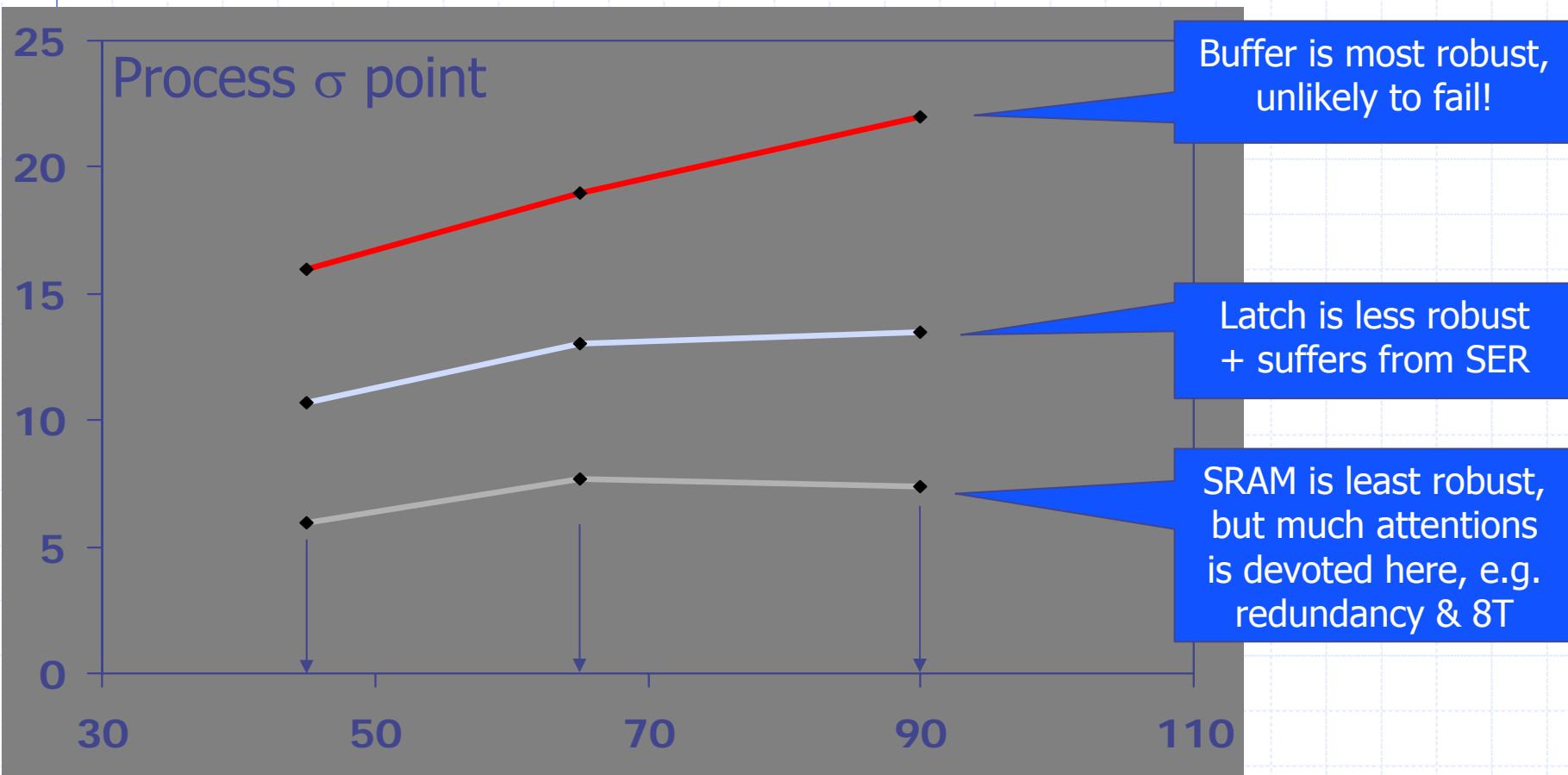
Technology Trend for an SRAM

- ◆ SRAM is known to be a more sensitive circuit... (lower σ).
- ◆ But, circuit heavily optimized for each technology.
- ◆ Much lower σ values + similar trend in sigma!



Comparison of Circuits (@Point C)

- ◆ Technology trend is modulated by circuit innovation and investment in analysis and optimization tools.
- ◆ Global trend remains clear!



Variability and Resilience

- ◆ We will likely need wide-spread resilience at and beyond the 32nm technology node.
- ◆ How much resilience and/or adaptation will be determined by how well we understand the fabrication process.
 - Firm understanding of the sources and impact of systematic variation is needed.
 - Magnitude of random or un-modeled variation will determine design margins (and design profit).
 - Models are critical to both!

Role of Modeling

- ◆ Modeling needs to become more aware of systematic and random variability.
 - As do other parts of the analysis flow, e.g. layout extraction.

- ◆ We need the ability to mix empirical and physical capabilities in a clean manner...
 - As we learn to make better characterization structures, the opportunity for early semi-empirical modeling will expand!

Ultimate Vision

Enable accurate model to hardware correlation and sophisticated design adaptation.

